

SOT-223 DEVICES (continued)

Plastic-Encapsulated High-Voltage Transistors

Pinout: 1-Base, 2-Collector, 3-Emitter, 4-Collector

Device	Marking	$V_{(BR)CEO}$	h_{FE}		f_T	
			Min	Max	@ I_C (mA)	Min (MHz)
NPN						
<i>BSP19AT1</i>	SP19A	350	40	—	20	70
<i>PZTA42T1</i>	P1D	300	40	—	10	50
<i>BF720T1</i>	BF720	250	50	—	10	60
<i>BSP20AT1</i>	SP20A	250	40	—	20	70
PNP						
<i>PZTA96T1</i>	ZTA96	450	50	150	10	50
<i>PZTA92T1</i>	P2D	300	40	—	10	50
<i>BSP16T1</i>	BSP16	300	30	150	10	15
<i>BF721T1</i>	BF721	250	50	—	10	60

Plastic-Encapsulated High Current Transistors

Pinout: 1-Base, 2-Collector, 3-Emitter, 4-Collector

Device	Marking	$V_{(BR)CEO}$	$V_{CE(sat)}$ Volts	$h_{FE@ I_C}$		
				Min	Max	mA
NPN						
<i>PZT651T1</i>	651	60	0.5	75	—	1000
<i>BCP68T1</i>	CA	20	0.5	60	—	1000
PNP						
<i>PZT751T1</i>	ZT751	60	0.5	75	—	1000
<i>BCP69T1</i>	CE	20	0.5	60	—	1000

Medium Power TMOS FETs

The following is a listing of medium power TMOS FETs which exhibit low $R_{DS(on)}$ characteristics.

Pinout: 1-Gate, 2-Drain, 3-Source, 4-Drain



$V_{(BR)DSS}$ (Volts) Min	$R_{DS(on)}$ (Ohms) @ Max	I_D (Amps)	Device	Marking	I_D (cont) Amps	$P_D^{(1)}$ (Watts) Max	Applications
N-Channel							
100	0.30	0.5	<i>MMFT1N10E</i>	1N10	1	0.8 ⁽³⁾	dc-dc Converters Power Supplies Motor Controls, Disk Drives
60	0.18	0.75	<i>MMFT3055EL</i>	3055L	1.5		
	0.15	0.85	<i>MMFT3055E</i>	3055E	1.7		
20	0.15	1	<i>MMFT2N02EL</i>	2N02L	2		
P-Channel							
60	0.30	0.6	<i>MMFT2955E</i>	2955E	1.2	0.8 ⁽³⁾	dc-dc Converters Power Supplies Motor Controls, Disk Drives

⁽¹⁾ $T_C = 25^\circ C$

⁽³⁾ Power rating when mounted on an FR-4 glass epoxy printed circuit board with the minimum pad size recommended.

See Packaging Information under Technical Data Section for reel size, quantity and ordering information.

Devices listed in bold, italic are Motorola preferred devices.